IN THE CLAIMS

Please amend claims 29, 30, and 33 as follows:

Claims 1 -28. (Canceled)

29. (Currently Amended) A flat panel display, comprising a plurality of sub-pixels driven by thin film transistors, each of the thin film transistors including a source electrode, a drain electrode, a gate electrode, and a polysilicon semiconductor layer and each of the sub-pixels including a first electrode, a second electrode, and an emitting layer disposed between the first electrode and the second electrode, wherein one of the source electrode and the drain electrode includes:

a first titanium layer contacting the semiconductor layer;

an aluminum-based metal layer arranged on the first titanium layer;

a second titanium layer arranged on the aluminum-based metal layer and contacting the first electrode;

a first titanium nitride layer disposed between the first titanium layer and the aluminum-based metal layer, the first titanium nitride layer preventing titanium from the first titanium layer and aluminum from the aluminum-based metal layer reacting with each other; and

a second titanium nitride layer disposed between the second titanium layer and the aluminum-based metal layer, the second titanium nitride layer preventing titanium from

the second titanium layer and aluminum from the aluminum-based metal layer reacting with each other;

wherein the titanium nitride ~~layer contains~~ layers contain 5 to 85wt% of nitrogen.

30. (Currently Amended) The flat panel display of claim 29, wherein the first titanium nitride layer has a thickness of about 100 to 600Å.

31. (Previously Presented) The flat panel display of claim 29, wherein the first titanium nitride layer has a thickness of about 100 to 400Å.

32. (Previously Presented) The flat panel display of claim 29, wherein the second titanium nitride layer has a thickness of about 200 to 600Å.

33. (Currently Amended) The flat panel display of claim 29, wherein the second titanium nitride ~~layers have~~ layer has a thickness of about 300Å.

34. (Previously Presented) A flat panel display, comprising a plurality of sub-pixels driven by thin film transistors, each of the thin film transistors including a source electrode, a drain electrode, a gate electrode, and a polysilicon semiconductor layer each of the sub-pixels including a first electrode, a second electrode, and an emitting layer disposed

between the first electrode and the second electrode, wherein one of the source electrode and the drain electrode includes:

a first titanium layer contacting the semiconductor layer;

an aluminum-based metal layer arranged on the first titanium layer;

a second titanium layer arranged on the aluminum-based metal layer and contacting the first electrode;

a first titanium nitride layer disposed between the first titanium layer and the aluminum-based metal layer, the first titanium nitride layer preventing titanium from the first titanium layer and aluminum from the aluminum-based metal layer reacting with each other; and

a second titanium nitride layer disposed between the second titanium layer and the aluminum-based metal layer, the second titanium nitride layer preventing titanium from the second titanium layer and aluminum from the aluminum-based metal layer reacting with each other;

wherein the aluminum-based metal layer is an aluminum alloy containing about 0.5 to 5 wt% of one element being selected from the group consisting of silicon, copper, neodymium, platinum, and nickel.

35. (Previously Presented) The flat panel display of claim 34, wherein the aluminum-based metal layer is an aluminum-silicon alloy containing about 2 wt% of silicon.